Abstracts

A Four Stage V-Band MOCVD HEMT Amplifier

W. Yau, E.T. Watkins, S.K. Wang, K. Wang and B. Klatskin. "A Four Stage V-Band MOCVD HEMT Amplifier." 1987 MTT-S International Microwave Symposium Digest 87.2 (1987 Vol. II [MWSYM]): 1015-1018.

V-band multi-stage Low Noise Amplifiers (LNA) were developed utilizing MOCVD High Electron Mobility Transistors (HEMTs). The amplifiers have demonstrated 16.57 dB gain with an associated noise figure of 5.65 dB and over 19 dB gain with 7.91 dB noise figure at 60.4 GHz. Another amplifier achieved over 5GHz bandwidth with greater than 14dB gain. The amplifier is integrated in a single housing that is 1.75 inch long.

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